

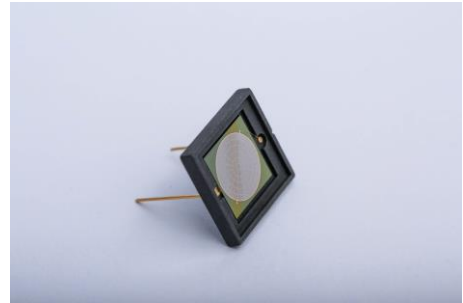


VUV photodiode

Model **SCT-VUV64**

General Features:

- SiC-based vacuum ultraviolet (VUV) photodiode
- Excellent stability under high fluence VUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- High detection efficiency for 193 nm VUV radiation
- Ceramic package

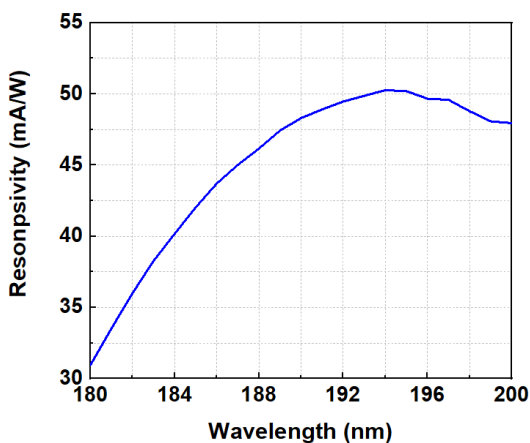


Applications: VUV radiation flux measurement, 193 nm excimer laser monitoring

Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T_{opt}	-20-80	°C
Storage temperature range	T_{sto}	-55-90	°C
Soldering temperature (3 s)	T_{sol}	260	°C
Maxium reverse voltage	V_{r-max}	-20	V
Electro-Optical characteristics (25 °C)			
Effective photo-sensitive area	A	63.5	mm ²
Responsivity (@193 nm)	R	50	mA/W
Dark current (@-1 V)	I_d	< 100	pA
Shunt resistance (@±10 mV)	R_{sh}	> 10	>
Capacitance (@ 0 V and 1 MHz)	C_p	2.4	nF
Rise time ($V_r=0$ V, $R_L=50$)	t_r	< 2	S

Spectral response



Package dimensions

